

G2R325MS65-CAL

6500 V 325 mΩ SiC MOSFET



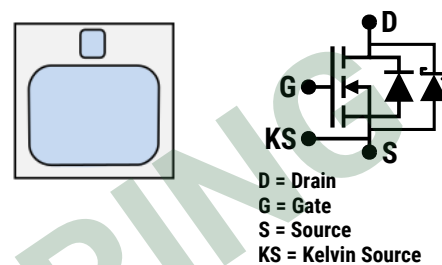
Silicon Carbide MOSFET with Integrated Schottky Diode N-Channel Enhancement Mode

V_{DS}	=	6500 V
$R_{DS(ON)(Typ.)}$	=	325 mΩ
$I_D (T_C = 115^\circ C)$	=	10 A

Features

- G2R™ Technology - +20 V / -5 V Gate Drive
- Superior $Q_G \times R_{DS(ON)}$ Figure of Merit
- Low Capacitances and Low Gate Charge
- Normally-Off Stable Operation up to 175°C
- Fast and Reliable Integrated Schottky Diode
- High Avalanche and Short Circuit Ruggedness
- Low Conduction Losses at High Temperatures

Bare Chip



Advantages

- Increased Power Density for Compact System
- High Frequency Switching
- Reduced Losses for Higher System Efficiency
- Minimized Gate Ringing
- Improved Thermal Capability
- Superior Cost-Performance Index
- Ease of Paralleling without Thermal Runaway
- Simple to Drive

Applications

- High Voltage Converters
- Smart Grid and HVDC
- Traction
- Pulsed Power

Absolute Maximum Ratings (At $T_C = 25^\circ C$ Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Drain-Source Voltage	$V_{DS(max)}$	$V_{GS} = 0 V, I_D = 100 \mu A$	6500	V	
Gate-Source Voltage (Dynamic)	$V_{GS(max)}$		-10 / +25	V	
Gate-Source Voltage (Static)	$V_{GS(op)}$	Recommended Operation	-5 / +20	V	
Continuous Forward Current	I_D	$T_C = 25^\circ C, V_{GS} = -5 / +20 V$	15	A	Note. 2
		$T_C = 100^\circ C, V_{GS} = -5 / +20 V$	11		
		$T_C = 135^\circ C, V_{GS} = -5 / +20 V$	8		
Power Dissipation	P_D	$T_C = 25^\circ C$	315	W	Note. 2
Operating and Storage Temperature	T_j, T_{stg}		-55 to 175	°C	

Note 1: Pulse Width t_P Limited by $T_{j(max)}$

Note 2: Assuming $R_{thJC(max)} = 0.48^\circ C/W$ (insulated base-plate package)

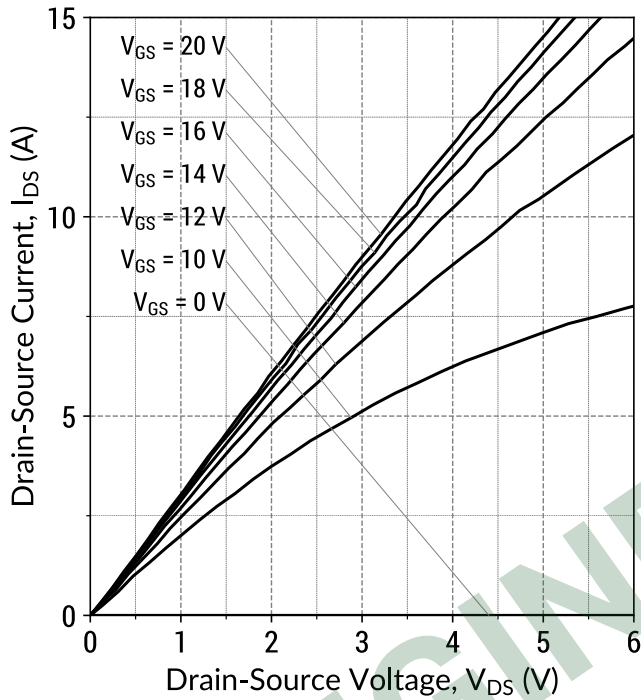
Electrical Characteristics (At $T_C = 25^\circ\text{C}$ Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	6500			V	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 6500\text{ V}, V_{GS} = 0\text{ V}$		1		μA	
Gate Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 25\text{ V}$			100	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = -10\text{ V}$			-100		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 6.0\text{ mA}$		2.7		V	Fig. 9
		$V_{DS} = V_{GS}, I_D = 6.0\text{ mA}, T_j = 175^\circ\text{C}$		1.71			
Transconductance	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 5\text{ A}$		2.5		S	Fig. 4
		$V_{DS} = 10\text{ V}, I_D = 5\text{ A}, T_j = 175^\circ\text{C}$		2.6			
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 20\text{ V}, I_D = 5\text{ A}$		325	406	mΩ	Fig. 5-8
		$V_{GS} = 20\text{ V}, I_D = 5\text{ A}, T_j = 175^\circ\text{C}$		1080			
Input Capacitance	C_{iss}			3395			
Output Capacitance	C_{oss}			80		pF	Fig. 10
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$		12.7			
C_{oss} Stored Energy	E_{oss}			31		μJ	Fig. 11
C_{oss} Stored Charge	Q_{oss}			110		nC	
Internal Gate Resistance	$R_{G(int)}$	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$		2		Ω	

Reverse Diode Characteristics

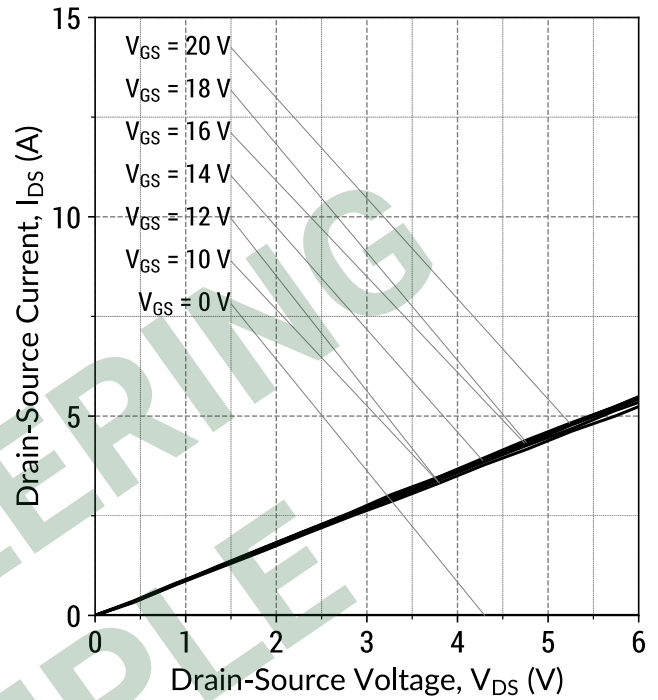
Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	V_{SD}	$V_{GS} = -5\text{ V}, I_{SD} = 5\text{ A}$		3.3		V	Fig. 12-13
		$V_{GS} = -5\text{ V}, I_{SD} = 5\text{ A}, T_j = 175^\circ\text{C}$		4.3			

Figure 1: Output Characteristics ($T_j = 25^\circ\text{C}$)



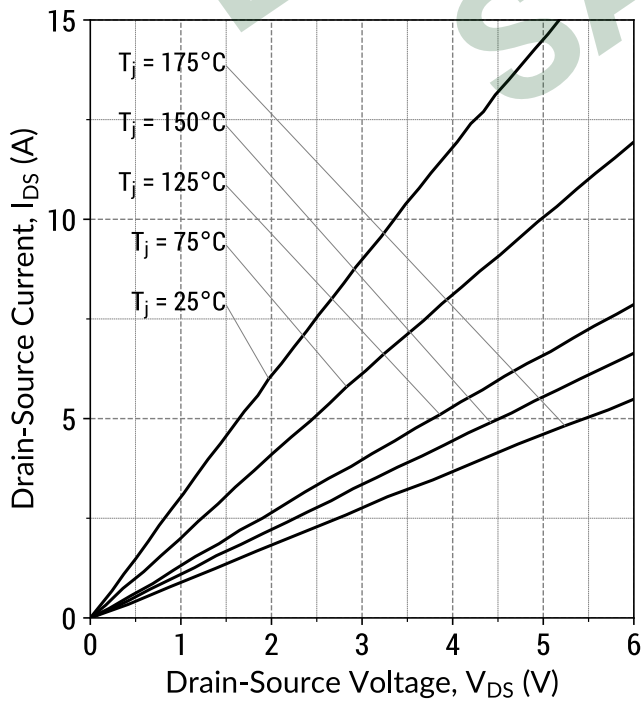
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 2: Output Characteristics ($T_j = 175^\circ\text{C}$)



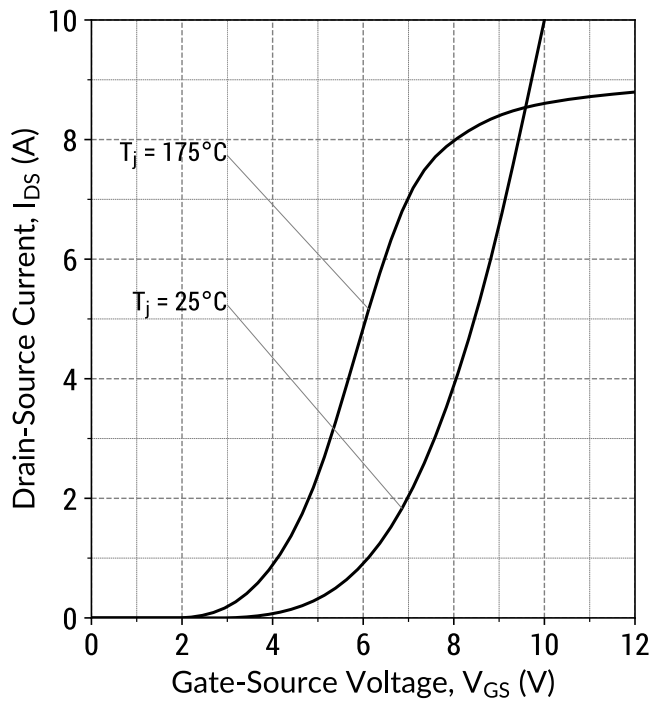
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 3: Output Characteristics ($V_{GS} = 20\text{ V}$)



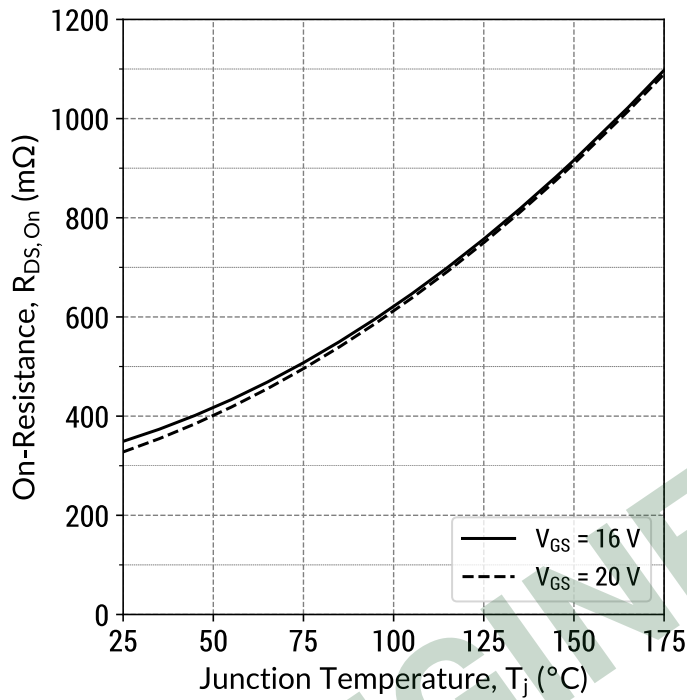
$I_D = f(V_{DS}, T_j); t_P = 250 \mu\text{s}$

Figure 4: Transfer Characteristics ($V_{DS} = 10\text{ V}$)



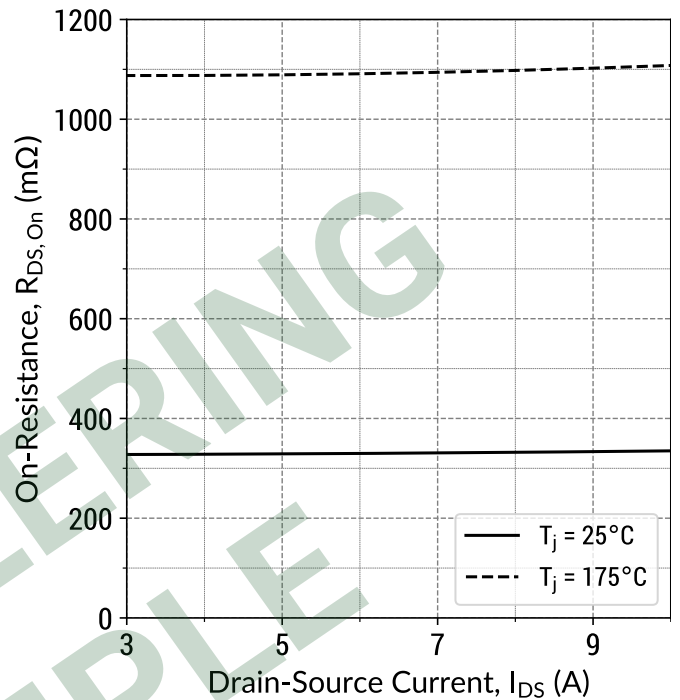
$I_D = f(V_{GS}, T_j); t_P = 100 \mu\text{s}$

Figure 5: On-State Resistance v/s Temperature



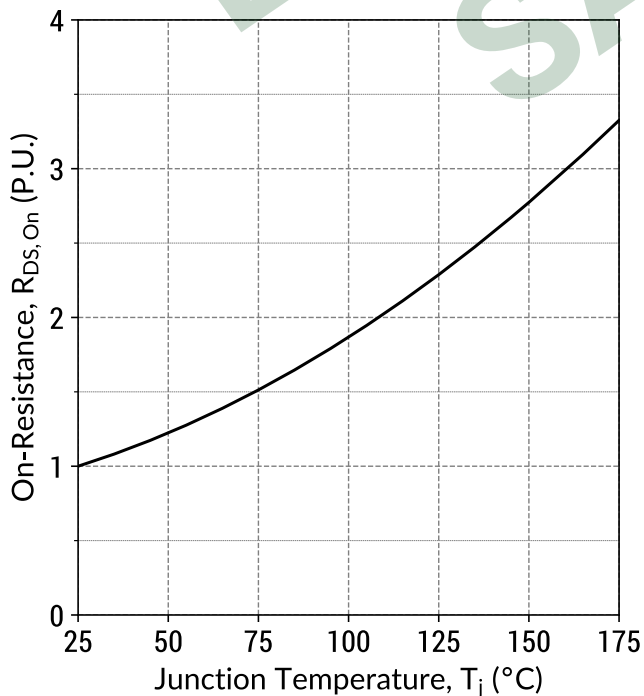
$R_{DS(ON)} = f(T_j, V_{GS}); t_P = 250\ \mu\text{s}; I_D = 5\text{ A}$

Figure 6: On-State Resistance v/s Drain Current



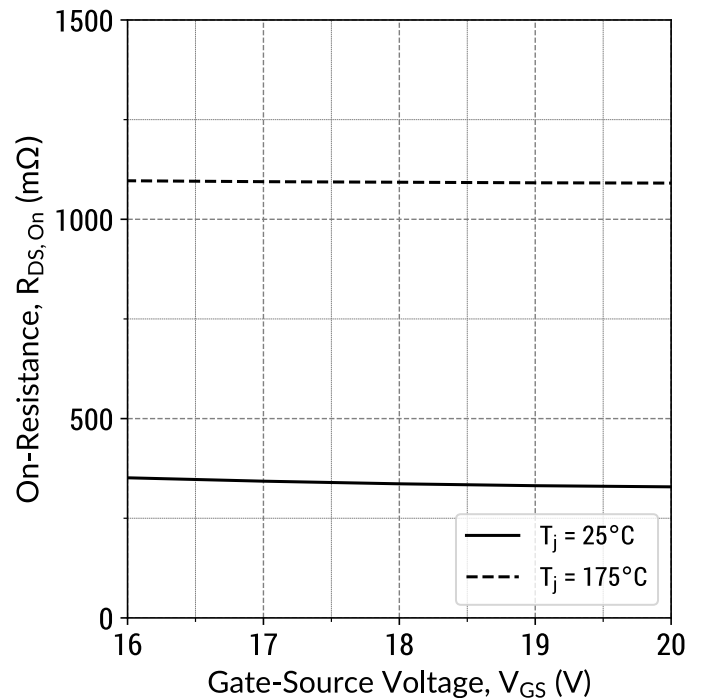
$R_{DS(ON)} = f(T_j, I_D); t_P = 250\ \mu\text{s}; V_{GS} = 20\text{ V}$

Figure 7: Normalized On-State Resistance v/s Temperature



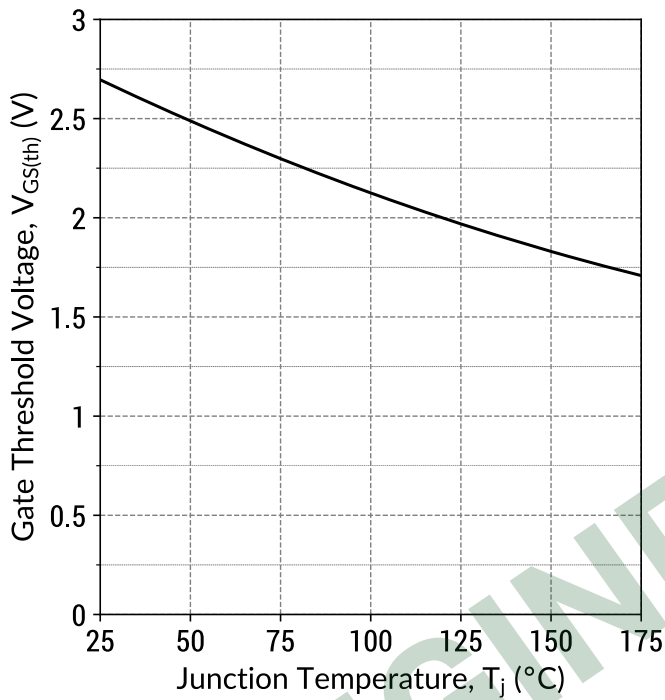
$R_{DS(ON)} = f(T_j); t_P = 250\ \mu\text{s}; I_D = 5\text{ A}; V_{GS} = 20\text{ V}$

Figure 8: On-State Resistance v/s Gate Voltage



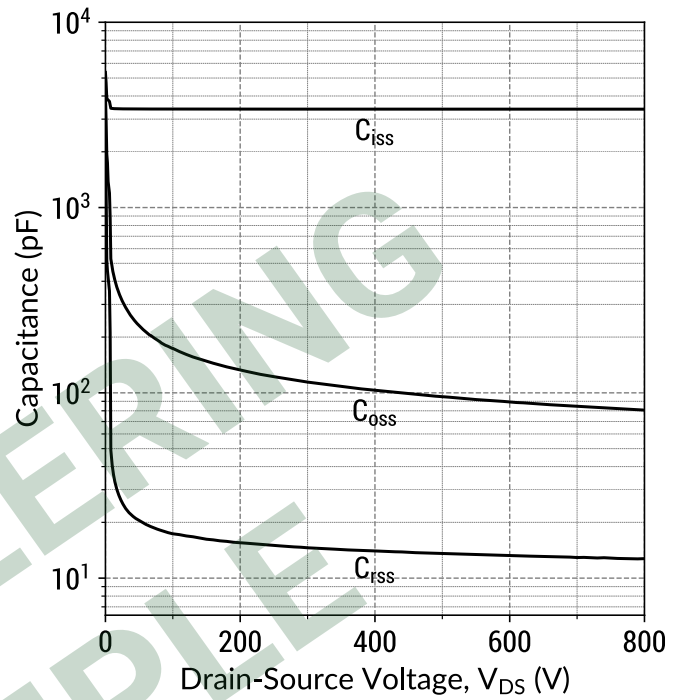
$R_{DS(ON)} = f(T_j, V_{GS}); t_P = 250\ \mu\text{s}; I_D = 5\text{ A}$

Figure 9: Threshold Voltage Characteristics



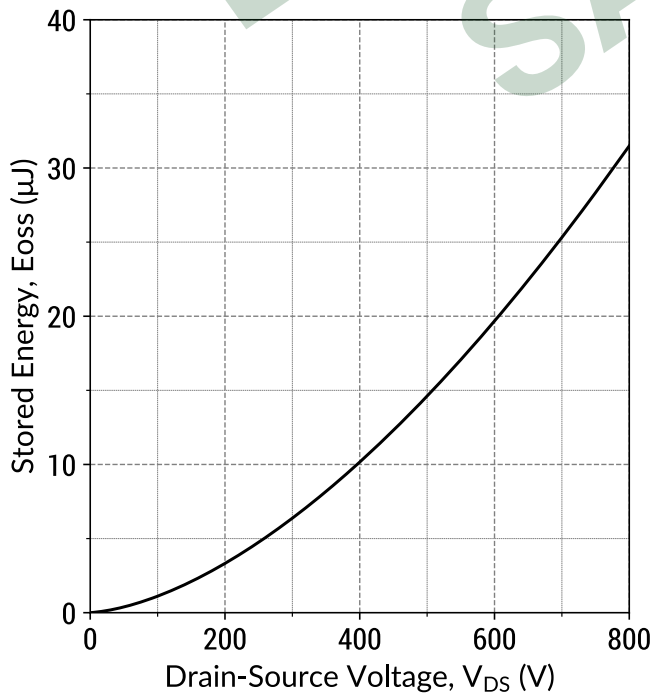
$V_{GS(th)} = f(T_j)$; $V_{DS} = V_{GS}$; $I_D = 6.0$ mA

Figure 10: Capacitance v/s Drain-Source Voltage



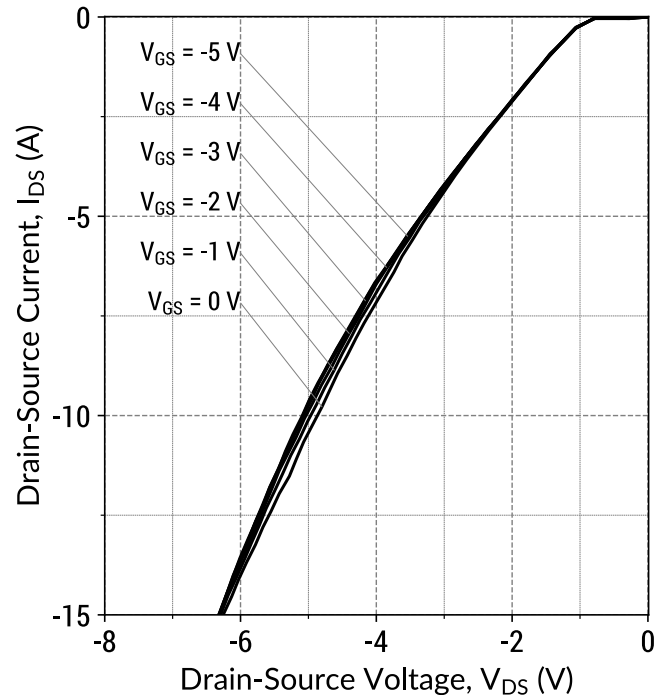
$f = 1$ MHz; $V_{AC} = 25$ mV

Figure 11: Output Capacitor Stored Energy



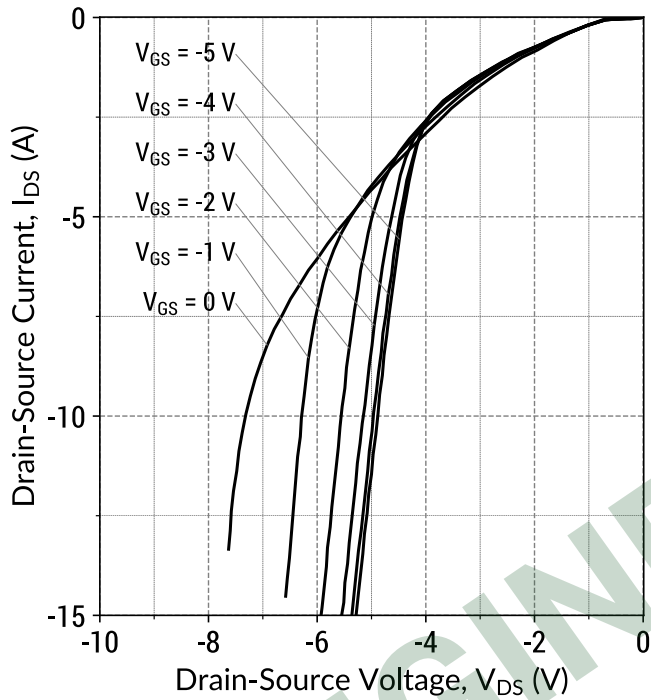
$E_{oss} = f(V_{DS})$

Figure 12: Body Diode Characteristics ($T_j = 25^\circ\text{C}$)



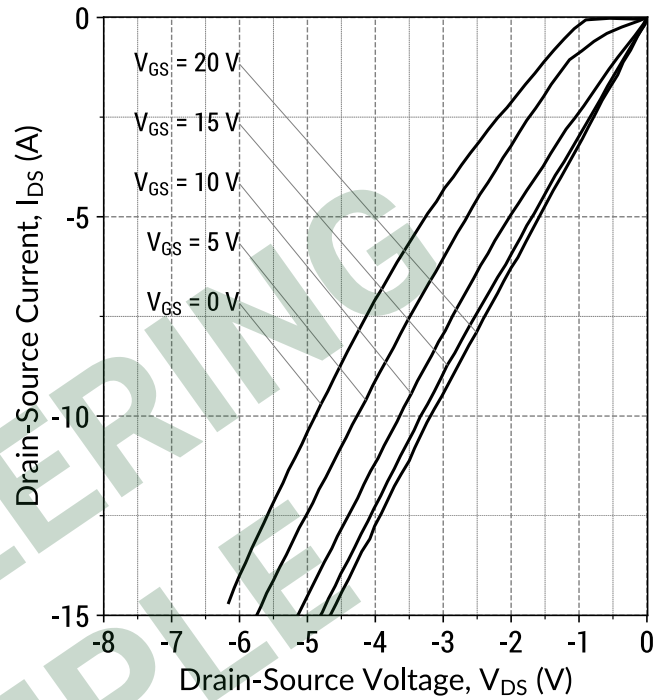
$I_D = f(V_{DS}, V_{GS})$; $t_P = 250$ μs

Figure 13: Body Diode Characteristics ($T_j = 175^\circ\text{C}$)



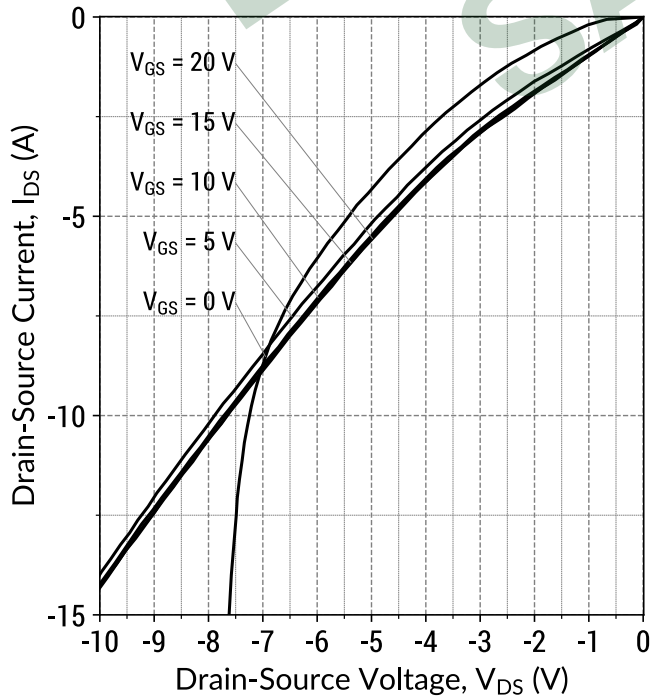
$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 14: Third Quadrant Characteristics ($T_j = 25^\circ\text{C}$)



$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Figure 15: Third Quadrant Characteristics ($T_j = 175^\circ\text{C}$)



$I_D = f(V_{DS}, V_{GS}); t_P = 250 \mu\text{s}$

Mechanical Parameters

This information is **confidential**, please contact sales@genesicsemi.com to learn more.

Chip Dimensions

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ENGINEERING
SAMPLE

NOTE

1. CONTROLLED DIMENSION IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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Related Links

- SPICE Models: https://www.genesicsemi.com/sic-mosfet/G2R325MS65-CAL/G2R325MS65-CAL_SPICE.zip
- PLECS Models: https://www.genesicsemi.com/sic-mosfet/G2R325MS65-CAL/G2R325MS65-CAL_PLECS.zip
- CAD Models: https://www.genesicsemi.com/sic-mosfet/G2R325MS65-CAL/G2R325MS65-CAL_3D.zip
- Gate Driver Reference: <https://www.genesicsemi.com/technical-support>
- Evaluation Boards: <https://www.genesicsemi.com/technical-support>
- Reliability: <https://www.genesicsemi.com/reliability>
- Compliance: <https://www.genesicsemi.com/compliance>
- Quality Manual: <https://www.genesicsemi.com/quality>

Revision History

Date	Revision	Comments	Supersedes
Sep. 28, 2020	Rev 1	Initial Release	



www.genesicsemi.com/sic-mosfet/